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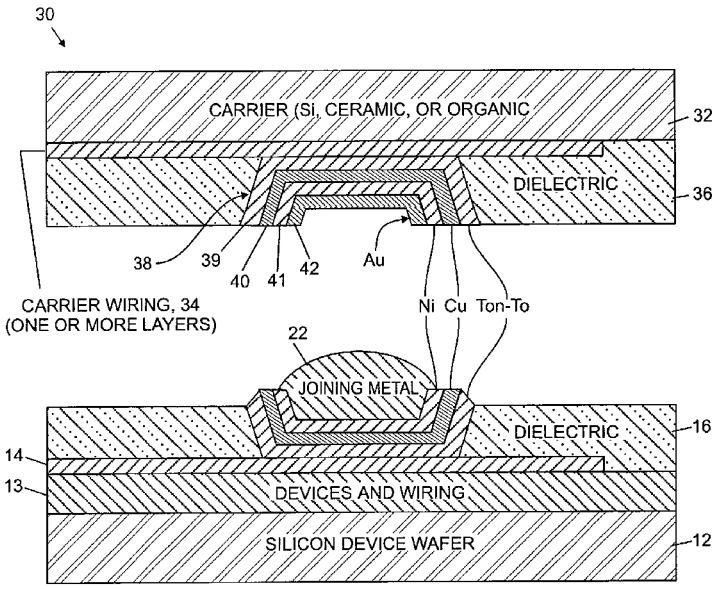
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(54) Title: HIGH DENSITY AREA ARRAY SOLDER MICROJOINING INTERCONNECT STRUCTURE AND FABRICATION METHOD



(57) Abstract: A system for interconnecting a set of device chips by means of an array of microjoints disposed on an interconnect carrier is taught. The carrier is provided with a dense array of microjoint receptacles with an adhesion layer, barrier layer and a noble metal layer; the device wafers are fabricated with an array of microjoining pads comprising an adhesion layer, barrier layer and a fusible solder layer with pads being located at matching locations in reference to the barrier receptacles; said device chips are joined to said carrier through the microjoint arrays resulting in interconnections capable of very high input/output density and inter-chip wiring density.

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